

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A semiconductor device comprising:

a conductive layer with a plurality of wires; and

a bonding pad formed in a region overlapping ~~with~~ the plurality of wires ~~of the~~
~~conductive layer,~~

wherein:

one of the plurality of wires is connected to the bonding pad, and a protective film with
an insulating property is formed between remaining ones of the plurality of wires and the
bonding pad; and

the protective film bridges ~~formed on said remaining ones of the plurality of wires is~~
~~bridged between~~ adjacent ones of said remaining ones of the plurality of wires at least in a region
overlapping with the bonding pad so that a void is formed in the protective film between the
adjacent ones of said remaining ones of the plurality of wires.

2. (Original) The semiconductor device as set forth in claim 1, wherein an insulating film
is formed between the protective film and the bonding pad, so as to cover the protective film.

3. (Original) The semiconductor device as set forth in claim 2, wherein the insulating film
is an oxide film formed by a chemical vapor deposition method.

4. (Original) The semiconductor device as set forth in claim 3, wherein the oxide film contains at least one of boron and phosphor.

5. (Currently amended) A semiconductor device comprising:
a conductive layer with a plurality of wires; and
a bonding pad formed in a region overlapping with the plurality of wires of the
conductive layer,
wherein:
at least one of the plurality of wires is connected to the bonding pad, and a protective film
with an insulating property is formed between remaining ones of the plurality of wires and the
bonding pad;
the protective film formed on said remaining ones of the plurality of wires is bridged
between adjacent ones of said remaining ones of the plurality of wires at least in a region
overlapping with the bonding pad; and

~~The semiconductor device as set forth in claim 1, wherein,~~ in a region where the protective film is bridged, a minimum value S1 of wire distance between adjacent ones of said remaining ones of the plurality of wires, and/or a length L1 of a bridged portion of the protective film are adjusted to suppress scattering and spouting at a void formed by the bridging of the protective film.

6. (Original) The semiconductor device as set forth in claim 5, wherein the minimum value S1 of wire distance and/or the length L1 of the bridged portion are adjusted so that the minimum value S1 is not less than 1.8 μ m, and the length L1 is not more than 900 μ m, or the

minimum value S1 of wire distance and/or the length L1 of the bridged portion are adjusted so that the minimum value S1 is within a range of from not less than $1.2\mu\text{m}$ to less than $1.8\mu\text{m}$, and the length L1 is not more than $1400\mu\text{m}$.

7. (Original) The semiconductor device as set forth in claim 6, wherein the minimum value S1 of wire distance and/or the length L1 of the bridged portion are adjusted so that the minimum value S1 is not less than $1.8\mu\text{m}$, or the length L1 of the bridged portion is not more than $400\mu\text{m}$.

8. (Original) The semiconductor device as set forth in claim 5, wherein the minimum value S1 and/or the length L1 are adjusted in a region other than the region overlapping with the bonding pad.

9. (Original) The semiconductor device as set forth in claim 1,
wherein the conductive layer comprises a second wiring layer that is formed on a semiconductor substrate having an active region where a semiconductor element is formed, and on a first wiring layer, via an interlayer insulating film, that is electrically connected to the active region, and

wherein the bonding pad is formed to overlap at least partially with the active region.

10-18. (Canceled)

19. (New) The semiconductor device of claim 1, wherein a void is formed in the protective film at least between adjacent first and second of the remaining ones of the plurality of wires in a region overlapping with the bonding pad.

20. (New) A semiconductor device comprising:
a conductive layer with a plurality of wires; and
a bonding pad formed in a region at least partially overlapping with the plurality of wires of the conductive layer,
wherein:
at least one of the plurality of wires is connected to the bonding pad, and a protective film with an insulating property is formed between remaining ones of the plurality of wires and the bonding pad; and
the protective film formed on said remaining ones of the plurality of wires is bridged between adjacent ones of said remaining ones of the plurality of wires at least in a region overlapping with the bonding pad so that a void is formed in the protective film at least between adjacent first and second of the remaining ones of the plurality of wires at least in a region overlapping with the bonding pad.